Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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1. TYPE RTU002P02

2. STRUCTURE SILICON P-CHANNEL MOS FET

3. APPLICATIONS SWITCHING

4. ABSOLUTE MAXIMUM RATINGS [Ta=25°C]

DRAIN-SOURCE VOLTAGE		VDSS	・・・	-20V
GATE-SOURCE VOLTAGE		VGSS	・・・	± 12V
DRAIN CURRENT	CONTINUOUS	ID	・・・	± 0.25A
	PULSED	IDP	・・・	± 0.5A PW≦10μs DUTY CYCLE≦1%
TOTAL POWER DISSIPATION		PD	・・・	0.2W EACH TERMINAL MOUNTED ON A RECOMMENDED LAND
CHANNEL TEMPERATURE		Tch	・・・	150°C
RANGE OF STRAGE TEMPERATURE		Tstg	・・・	−55~150°C

5. THERMAL RESISTANCE

CHANNEL TO AMBIENT		Rth(ch-a)	・・・	625°C/W EACH TERMINAL MOUNTED ON A RECOMMENDED LAND

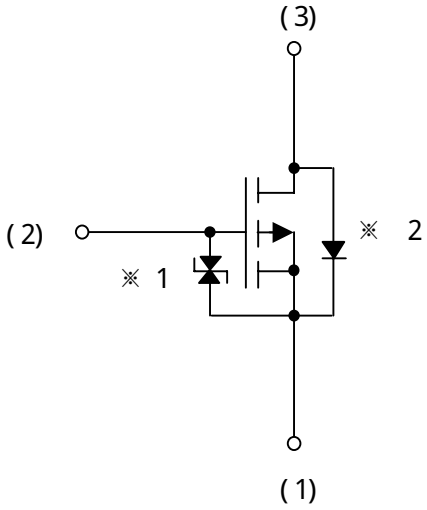
6. ELECTRICAL CHARACTERISTICS [Ta=25°C]

PARAMETER	ITEM	CONDITION	MIN.	TYP.	MAX.
GATE-SOURCE LEAKAGE	IGSS	VGS=± 12V / VDS=0V	-	-	± 10μA
DRAIN-SOURCE BREAKDOWN VOLTAGE	V(BR)DSS	ID=-1mA / VGS=0V	-20V	-	-
ZERO GATE VOLTAGE DRAIN CURRENT	IDSS	VDS=-20V / VGS=0V	-	-	-1μA
GATE THRESHOLD VOLTAGE	VGS(th)	VDS=-10V / ID=-1mA	-0.7V	-	-2.0V
STATIC DRAIN-SOURCE ON-STATE RESISTANCE	RDS(on) * PULSED	ID=-0.25A VGS=-4.5V	-	1.0Ω	1.5Ω
		ID=-0.25A VGS=-4.0V	-	1.1Ω	1.6Ω
		ID=-0.15A VGS=-2.5V	-	2.0Ω	3.0Ω
FORWARD TRANSFER ADMITTANCE	|Yfs| * PULSED	VDS=-10V ID=-0.15A	0.2S	-	-
INPUT CAPACITANCE	Ciss	VDS=-10V / VGS=0V f=1MHz	-	50pF	-
OUTPUT CAPACITANCE	Coss		-	5pF	-
REVERSE TRANSFER CAPACITANCE	Crss		-	5pF	-
TURN-ON DELAY TIME	td(on) * PULSED	ID=-0.15A VDD≒-15V VGS=-4.5V RL≒100Ω RGS=10Ω	-	9ns	-
RISE TIME	tr * PULSED		-	6ns	-
TURN-OFF DELAY TIME	td(off) * PULSED		-	35ns	-
FALL TIME	tf * PULSED		-	45ns	-

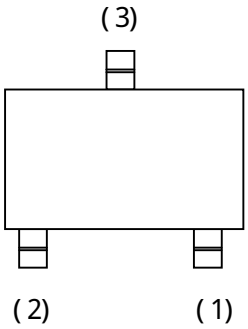
BODY DIODE CHARACTERISTICS (SOURCE-DRAIN CHARACTERISTICS) [Ta=25°C]

PARAMETER	ITEM	CONDITION	MIN.	TYP.	MAX.
FORWARD VOLTAGE	VSD	IS=-0.1A / VGS=0V	-	-	-1.2V

7. INNER CIRCUIT

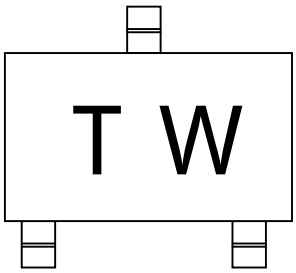


(1) SOURCE
(2) GATE
(3) DRAIN



※ 1 ESD PROTECTION DIODE
※ 2 BODY DIODE

8. MARKING



" TW" MEANS RTU002P02.